

BUV20

HIGH CURRENT NPN SILICON TRANSISTOR

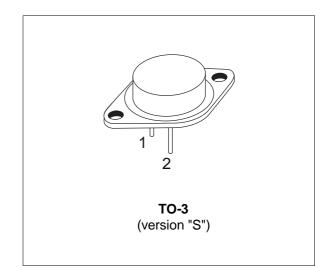
- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- HIGH RUGGEDNESS

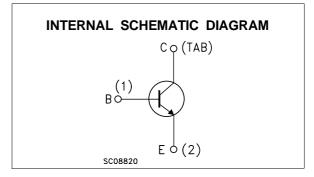
APPLICATIONS

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT
- SWITCHING REGULATORS

DESCRIPTION

The BUV20 is silicon Multiepitaxial Planar NPN transistor mounted in jedec TO-3 metal case. It is intended for use in switching and linear applications in military and industrial equipment.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	160	V
V_{CER}	Collector-Emitter Voltage ($R_{BE} = 100\Omega$)	150	V
V _{CEX}	Collector-Emitter Voltage (V _{BE} = -1.5V)	160	V
Vceo	Collector-Emitter Voltage (I _B = 0)	125	V
V _{EBO}	Emitter-Base Voltage $(I_C = 0)$	7	V
Ιc	Collector Current	50	Α
I _{CM}	Collector Peak Current	60	Α
IB	Base Current	10	Α
P _{tot}	Total Power Dissipation at $T_{case} \le 25$ $^{\circ}C$	250	W
T _{stg}	Storage Temperature	-65 to 200	°C
Tj	Junction Temperature	200	°C

THERMAL DATA

R _{thj-case} Thermal Resistance Junction-case	Max	0.7	°C/W
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{o}C$ unless otherwise specified)

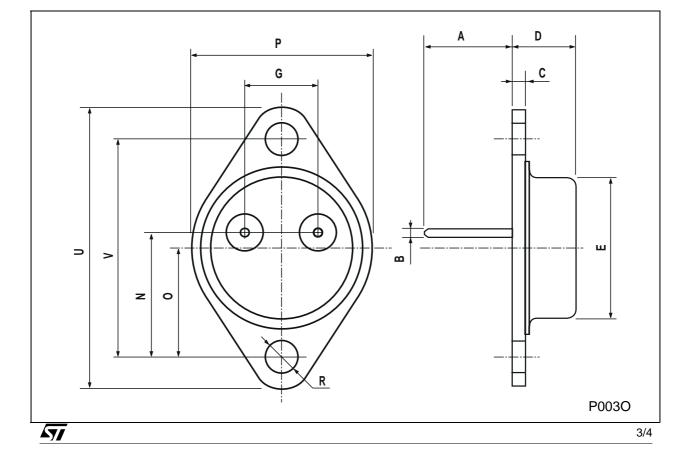
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CEX}	Collector Cut-off Current (V _{BE} = -1.5V)	$V_{CE} = 160 V$ $V_{CE} = 160 V$ $T_{case} = 125 °C$			3 12	mA mA
I _{CEO}	Collector Cut-off Current ($I_B = 0$)	V _{CE} = 100 V			3	mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = 5 V			1	mA
$V_{CEO(sus)^*}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 200 mA L = 25 mH	125			V
$V_{(BR)EB0}*$	Emitter-base Breakdown Voltage (I _C = 0)	I _E = 50 mA	7			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage			0.3 0.7	0.6 1.2	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	$I_{\rm C} = 50 \text{ A}$ $I_{\rm B} = 5 \text{ A}$		1.4	2	V
h _{FE} *	DC Current Gain	V _{CE} = 2 V I _C = 25 A V _{CE} = 4 V I _C = 50 A	20 10		60	
f⊤	Transition frequency	$V_{CE} = 15 \text{ V}$ I _C = 2 A f = 100 MHz	8			MHz
t _{on} t _f ts	RESISTIVE LOAD Turn-on Time Fall Time Storage Time	$I_{\rm C} = 50 \text{ A}$ $I_{\rm B1} = -I_{\rm B2} = 5 \text{ A}$			1.5 0.3 1.2	μs μs μs

* Pulsed: Pulse duration = 300 μ s, duty cycle \leq 2 %.

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DIM.		mm			inch	
Dim.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	11.00		13.10	0.433		0.516
В	1.47		1.60	0.058		0.063
С	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
Р	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193





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